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November 2013

### FQP30N06L

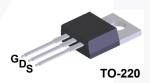
# N-Channel QFET<sup>®</sup> MOSFET 60 V, 32 A, 35 m $\Omega$

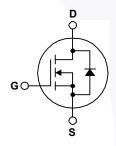
#### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

#### **Features**

- 32 A, 60 V,  $R_{DS(on)}$  = 35 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 16 A
- Low Gate Charge (Typ. 15 nC)
- Low Crss (Typ. 50 pF)
- · 100% Avalanche Tested
- · 175°C Maximum Junction Temperature Rating





#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQP30N06L	Unit
$V_{DSS}$	Drain-Source Voltage		60	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°	C)	32	Α
	- Continuous (T <sub>C</sub> = 100	)°C)	22.6	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	128	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 20	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	350	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	32	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	7.9	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	7.0	V/ns
$P_D$	Power Dissipation (T <sub>C</sub> = 25°C)		79	W
	- Derate above 25°C		0.53	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Ran	ige	-55 to +175	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

#### **Thermal Characteristics**

Symbol	Parameter	FQP30N06L	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	1.90	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

#### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP30N06L	FQP30N06L	TO-220	Tube	N/A	N/A	50 units

#### **Electrical Characteristics** $T_C = 25$ °C unless otherwise noted.

Parameter	Test Conditions	Min	Тур	Max	Unit
aracteristics					
Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60			V
Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C		0.06		V/°C
Zana Oata Valtana Basin Ourrant	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1	μΑ
Zero Gate voltage Drain Current	V <sub>DS</sub> = 48 V, T <sub>C</sub> = 150°C			10	μΑ
Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0 V	-		100	nA
Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -20 V, V <sub>DS</sub> = 0 V			-100	nA
	Drain-Source Breakdown Voltage Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate-Body Leakage Current, Forward	tracteristics         Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}$ , $I_D = 250 \text{ μA}$ Breakdown Voltage Temperature Coefficient $I_D = 250 \text{ μA}$ , Referenced to 25°C         Zero Gate Voltage Drain Current $V_{DS} = 60 \text{ V}$ , $V_{GS} = 0 \text{ V}$ $V_{DS} = 48 \text{ V}$ , $V_{CS} = 150 \text{ C}$ Gate-Body Leakage Current, Forward $V_{GS} = 20 \text{ V}$ , $V_{DS} = 0 \text{ V}$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	tracteristics       Drain-Source Breakdown Voltage $V_{GS} = 0 \text{ V}$ , $I_D = 250 \text{ μA}$ 60        Breakdown Voltage Temperature Coefficient $I_D = 250 \text{ μA}$ , Referenced to 25°C      0.06       Zero Gate Voltage Drain Current $V_{DS} = 60 \text{ V}$ , $V_{GS} = 0 \text{ V}$ $V_{DS} = 48 \text{ V}$ , $V_{CS} = 150 \text{ C}$ Gate-Body Leakage Current, Forward $V_{GS} = 20 \text{ V}$ , $V_{DS} = 0 \text{ V}$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

#### **On Characteristics**

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		2.5	V
R <sub>DS(on)</sub>	Static Drain-Source	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 16 A	-	0.027	0.035	0
	On-Resistance	$V_{GS} = 5 \text{ V}, I_{D} = 16 \text{ A}$		0.035	0.045	Ω
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 25 V, I <sub>D</sub> = 16 A	-	24		S

#### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$	 800	1040	pF
Coss	Output Capacitance	f = 1.0 MHz	 270	350	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		 50	65	pF

#### **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 16 A,		15	40	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		210	430	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	<u> </u>		60	130	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)	/	110	230	ns
$Q_g$	Total Gate Charge	V <sub>DS</sub> = 48 V, I <sub>D</sub> = 32 A,		15	20	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 5 V	A	3.5		nC
$Q_{gd}$	Gate-Drain Charge	(Note 4)		8.5		nC

#### **Drain-Source Diode Characteristics and Maximum Ratings**

$I_S$	Maximum Continuous Drain-Source Diode Forward Current				32	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				128	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 32 A			1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 32 A,		60		ns
Q <sub>rr</sub>	Reverse Recovery Charge	$dI_F / dt = 100 A/\mu s$		90		nC

- **Notes:** 1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. L = 400  $\mu$ H, I<sub>AS</sub> = 32 A, V<sub>DD</sub> = 25 V, R<sub>G</sub> = 25  $\Omega$ , starting T<sub>J</sub> = 25°C. 3. I<sub>SD</sub>  $\leq$  32 A, di/dt  $\leq$  300 A/us, V<sub>DD</sub>  $\leq$  BV<sub>DSS</sub>, starting T<sub>J</sub> = 25°C. 4.Essentially independent of operating temperature.

### **Typical Characteristics**

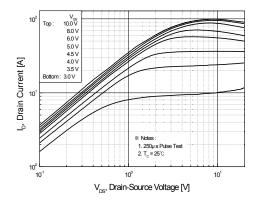


Figure 1. On-Region Characteristics

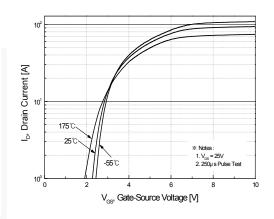


Figure 2. Transfer Characteristics

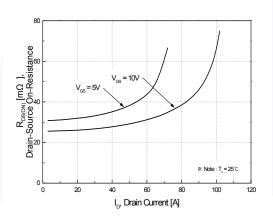


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

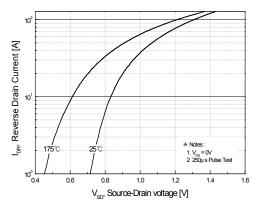


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

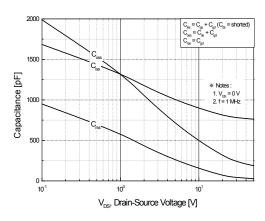


Figure 5. Capacitance Characteristics

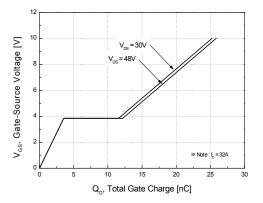


Figure 6. Gate Charge Characteristics

### Typical Characteristics (continued)

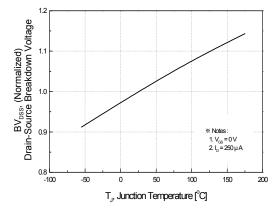


Figure 7. Breakdown Voltage Variation vs. Temperature

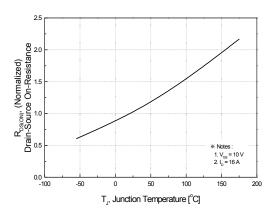


Figure 8. On-Resistance Variation vs. Temperature

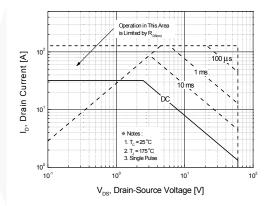


Figure 9. Maximum Safe Operating Area

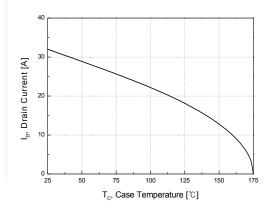


Figure 10. Maximum Drain Current vs. Case Temperature

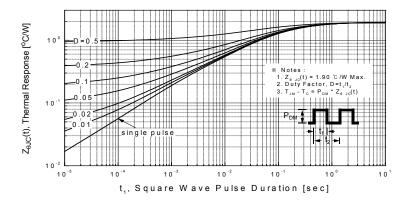


Figure 11. Transient Thermal Response Curve

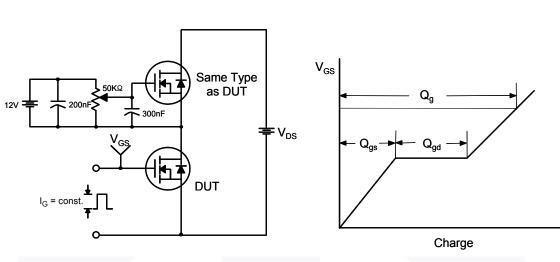


Figure 12. Gate Charge Test Circuit & Waveform

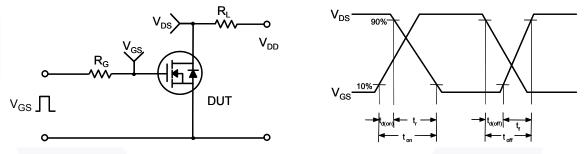


Figure 13. Resistive Switching Test Circuit & Waveforms

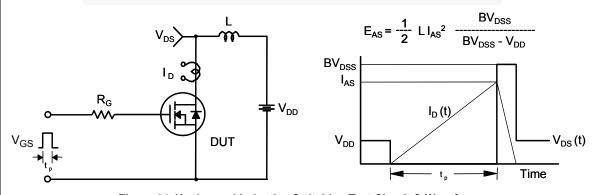
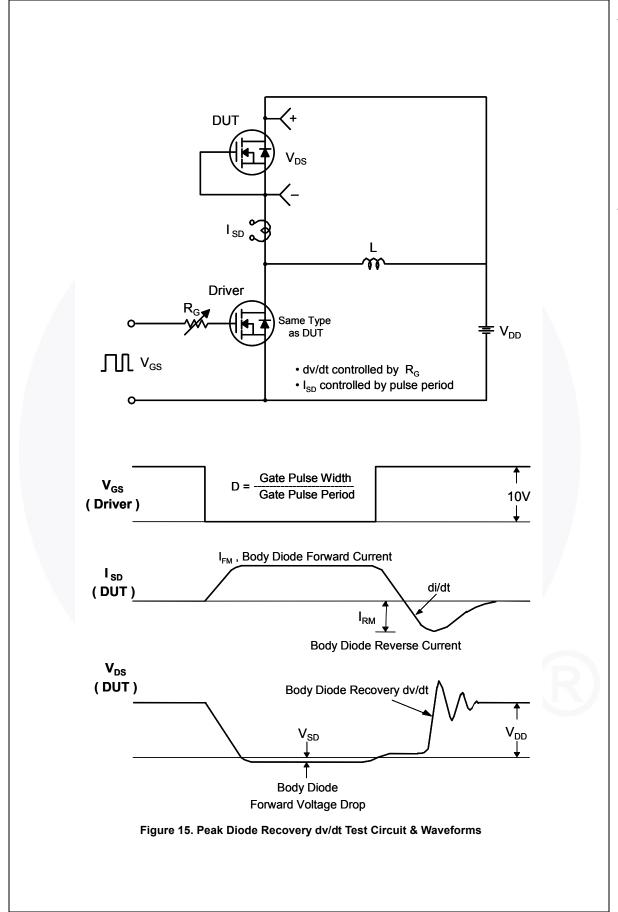


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



#### **Mechanical Dimensions**

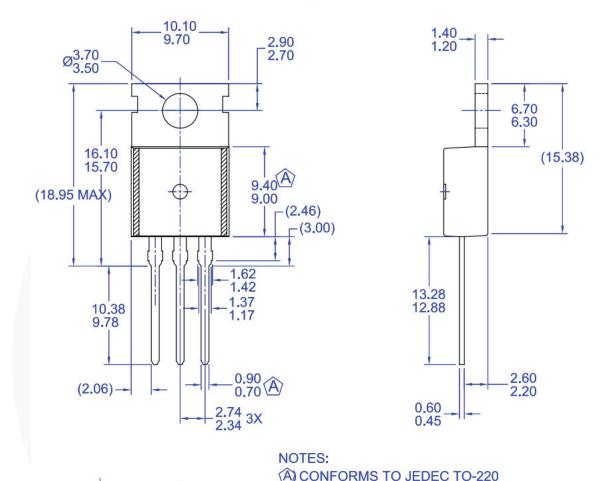


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

VARIATION AB EXCEPT WHERE NOTED

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D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

B) ALL DIMENSIONS ARE IN MILLIMETERS.

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4.70

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